

GaAs Semiconductor Laser Diode Fabry-Perot Laser

PRELIMINARY SPECIFICATION

#### **RW Laser**

# EYP-RWL-1080-00080-0750-SOT01-0000

General Product Information		
Product	Application	
1080 nm Fabry-Perot Laser	Spectroscopy	
sealed SOT Housing		
Monitor Diode		



#### **Absolute Maximum Ratings**

	Symbol	Unit	min	typ	max
Storage Temperature	$T_S$	°C	-20		85
Operational Temperature at Case	$T_C$	°C	-20		50
Forward Current	I <sub>F</sub>	mA			150
Reverse Voltage	$V_R$	V			0
Output Power	Popt	mW			90

Stress in excess of the Absolute Maximum Ratings can cause permanent damage to the device. Operation at the Absolute Maximum Rating for extended periods of time can adversely affect the device realibility and may lead to reduced operational life.

Recommend	led O	perational	l Condi	itions
110001111110114		por a trorra	90	

	Symbol	Unit	min	typ	max
Operational Temperature at case	T <sub>C</sub>	°C	15		40
Forward Current	I <sub>F</sub>	mA			130
Output Power	$P_{\rm opt}$	mW	10		80

## Characteristics at T<sub>amb</sub> 25 °C at Begin Of Life

Parameter	Symbol	Unit	min	typ	max
Center Wavelength	$\lambda_{C}$	nm	1070	1080	1090
Spectral Width (FWHM)	Δλ	nm			1
Temperature Coefficient of Wavelength	$d\lambda$ / $dT$	nm / K		0.3	
Output Power @ $I_F = 130 \text{ mA}$	$P_{\text{opt}}$	mW	80		
Slope Efficiency	$\eta_{\text{d}}$	W/A	0.6	0.8	1.2
Threshold Current	$I_{th}$	mA			70

Measurement Conditions / Comments
otal output measured with integrating sphere





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Characteristics at T <sub>amb</sub> 25 °C at Begin Of Life							
Parameter	Symbol	Unit	min	typ	max		
Operational Current @ P <sub>opt</sub> = 80 mW	l <sub>op</sub>	mA			130		
Cavity Length	L	μm		750			
Divergence parallel (FWHM)	$\Theta_{  }$	0		10			
Divergence perpendicular (FWHM)	$\Theta_{\perp}$	0		30			
Polarization				TE			
Spatial Mode (transversal)				TEM <sub>00</sub>			
Spectral Mode (longitudinal) Single/Multi Mode					ode		

Measurement Conditions / Comments	
E field parallel to Pin 2 - Pin 3 - plane	
Fundamental Mode	
depending on operating conditions	

Monitor Diode					
Parameter	Symbol	Unit	min	typ	max
Monitor Detector Responsivity	I <sub>mon</sub> / P <sub>opt</sub>	μA / mW	1		10
Reverse Voltage Monitor Diode	$U_RMD$	V	3		5

Measurement Conditions / Comments
$U_R = 5 \text{ V, target values}$



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#### PRELIMINARY SPECIFICATION

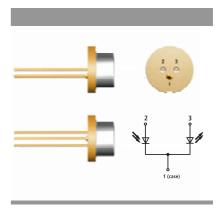
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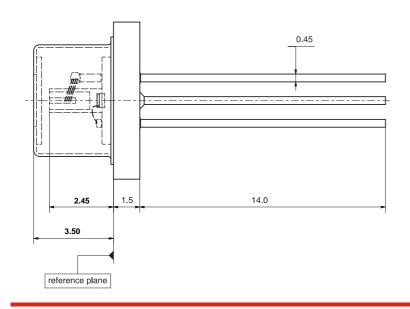
Package Dimensions					
	Symbol	Unit	min	typ	max
Height of Emission Plane	d <sub>EP</sub>	mm	2.30	2.45	2.50
Excentricity of Emission Center	R	mm			0.12
Pin Length		mm		14.0	

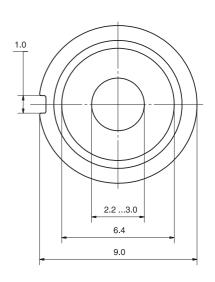
reference plane: top side of TO header
reference: center of outer diameter of header

Package Pinout	M-Type	
Ground	1	
Photo Diode (+)	2	
Laser (+)	3	



## Package Drawings







GaAs Semiconductor Laser Diode



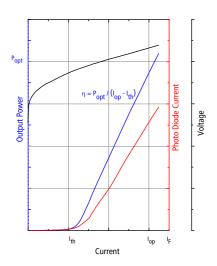
PRELIMINARY SPECIFICATION

#### **RW** Laser

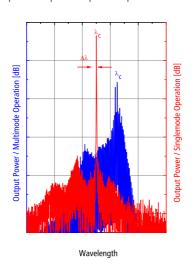
## EYP-RWL-1080-00080-0750-SOT01-0000

#### **Typical Measurement Results**

Output Power vs. Current



Spectra at Specified Optical Output Power



Performance figures, data and any illustrative material provided in this specification are typical and must be specifically confirmed in writing by eagleyard Photonics before they become applicable to any particular order or contract. In accordance with the eagleyard Photonics policy of continuous improvement specifications may change without notice.

#### Unpacking, Installation and Laser Safety

Unpacking the laser diodes should only be done at electrostatic safe workstations (EPA). Though protection against electro static discharge (ESD) is implemented in the laser package, charges may occur at surfaces. Please store this product in its original package at a dry, clean place until final use. During device installation, ESD protection has to be maintained.

The RWL diode type is known to be sensitive against thermal stress. Operating at moderate temperatures on propper heat sinks willl contribute to a long lifetime of the diode.

The laser emission from this diode is close to the invisible infrared region of the electromagnetic spectrum. Avoid direct and/or indirect exposure to the free running beam. Collimating the free running beam with optics as common in optical instruments will increase thread to the human eye.

Each laser diode will come with an individual test protocol verifying the parameters given in this document.



